

FNK N-Channel Enhancement Mode Power MOSFET

Description

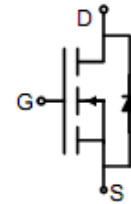
The FNK03N024A uses advanced trench technology and provide excellent $R_{DS(ON)}$ with low gate charge, it can be used in a wide variety of applications.

General Features

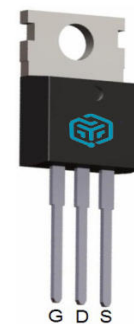
- $V_{DS} = 30V, I_D = 180A$
 $R_{DS(ON)} < 2.4m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 5.0m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply



Schematic diagram



To-220 Top View

PACKAGE MARKING AND ORDERING INFORMATION

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| FNK03N024A | FNK03N024A | TO-220 | | | |

ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|----------|------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous@ Current-Pulsed (Note 1) | $I_D(25^{\circ}C)$ | 180 | A |
| | I_{DM} | 720 | A |
| Maximum Power Dissipation | P_D | 140 | W |
| Single pulse avalanche energy(Note 5) | EAS | 300 | mJ |

| | | | |
|--|----------------|------------|--------------------|
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^{\circ}\text{C}$ |
|--|----------------|------------|--------------------|

THERMAL CHARACTERISTICS

| | | | |
|---|-----------------|------|----------------------|
| Thermal Resistance, Junction-to-Case (Note 2) | $R_{\theta JC}$ | 0.88 | $^{\circ}\text{C/W}$ |
|---|-----------------|------|----------------------|

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

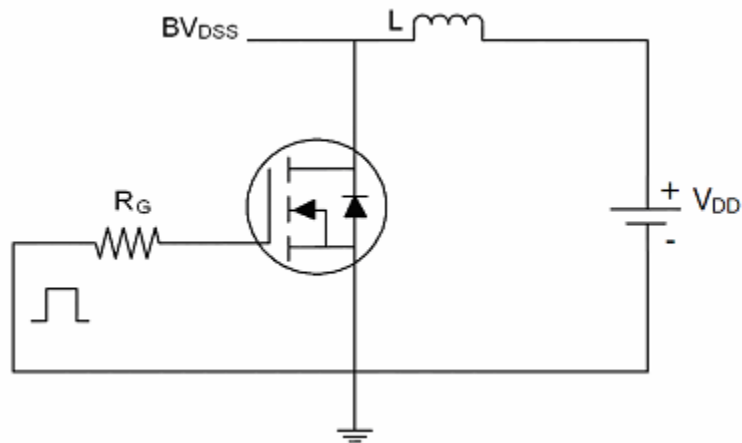
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|------------------------------------|---------------------|---|-----|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 30 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V, V _{GS} =0V | | | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | | | ±100 | nA |
| ON CHARACTERISTICS (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1.0 | 1.5 | 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =10A | | | 2.4 | mΩ |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =4.5V, I _D =6A | | | 5.0 | mΩ |
| DYNAMIC CHARACTERISTICS (Note4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =15V, V _{GS} =0V, F=1.0MHz | | 4945 | | PF |
| Output Capacitance | C _{oss} | | | 908 | | PF |
| Reverse Transfer Capacitance | C _{rss} | | | 493 | | PF |
| SWITCHING CHARACTERISTICS (Note 4) | | | | | | |
| Delay Time | t _{d(on)} | V _{DS} =15V, V _{DS} =10V, R _{GEN} =6Ω R _L =1Ω, I _D =50A | | 19 | | nS |
| Turn-on Rise Time | t _r | | | 94 | | nS |
| Turn-Off Delay Time | t _{d(off)} | | | 28 | | nS |
| Turn-Off Fall Time | t _f | | | 30 | | nS |
| Total Gate Charge | Q _g | V _{DS} =15V, I _D =20A, V _{GS} =10V | | 35 | | nC |
| Gate-Source Charge | Q _{gs} | | | 11 | | nC |
| Gate-Drain Charge | Q _{gd} | | | 10 | | nC |
| DRAIN-SOURCE DIODE CHARACTERISTICS | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V, I _S =40A | | | 1.2 | V |
| Diode Forward Current (Note 2) | I _S | | | | 40 | A |
| Reverse Recovery Time | trr | T _J = 25℃, I _F =90A di/dt = 100A/us (Note3) | | 47 | | ns |
| Reverse Recovery Charge | Qrr | | | 130 | | nc |

NOTES:

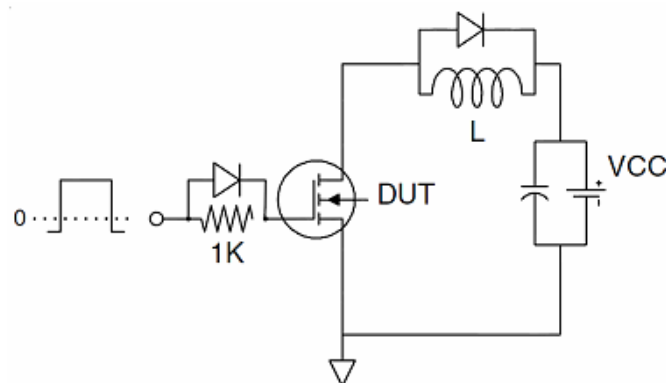
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in² FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing
5. EAS condition $T_J=25^{\circ}\text{C}$, $V_{DD}=15V$, $V_G=10V$, $L=0.5mH$, $R_g=25\Omega$

Test circuit

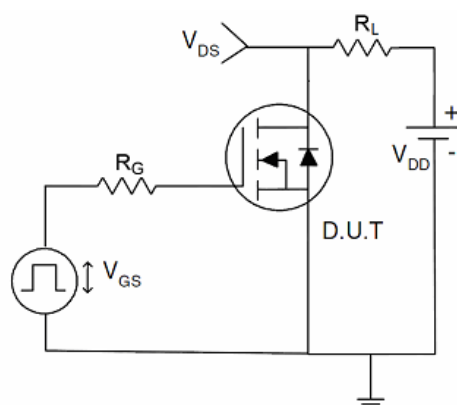
1) EAS test Circuits

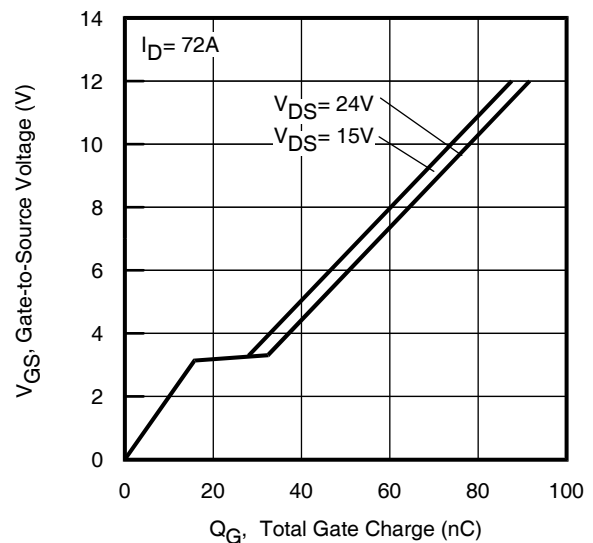
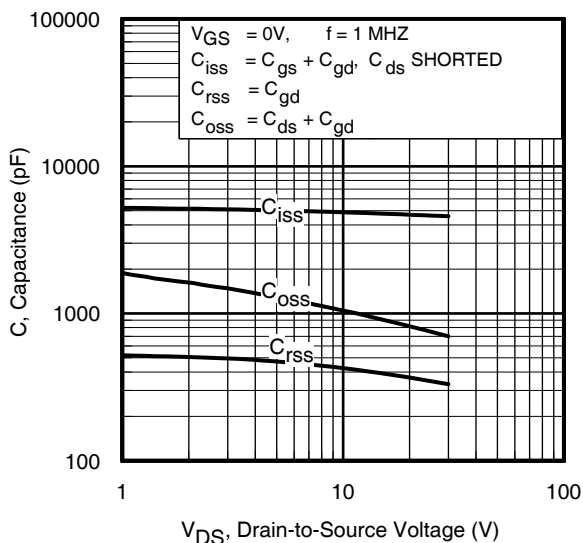
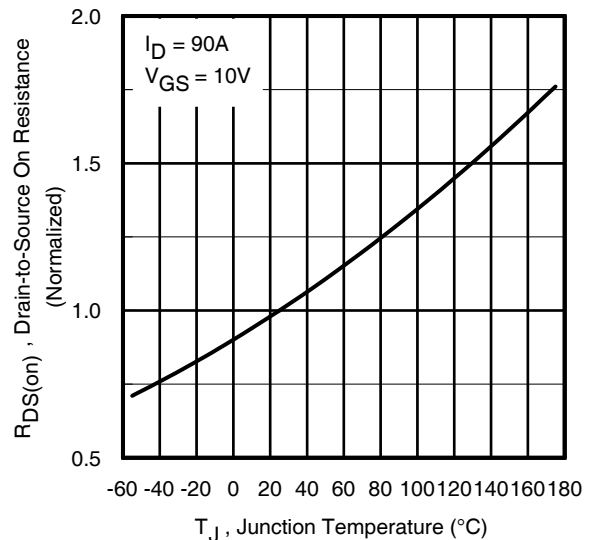
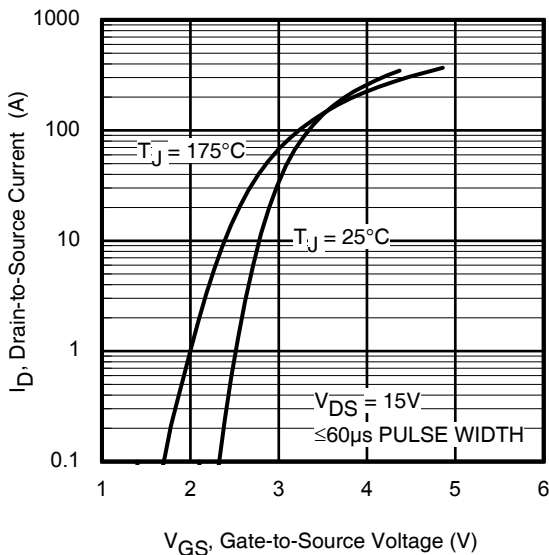
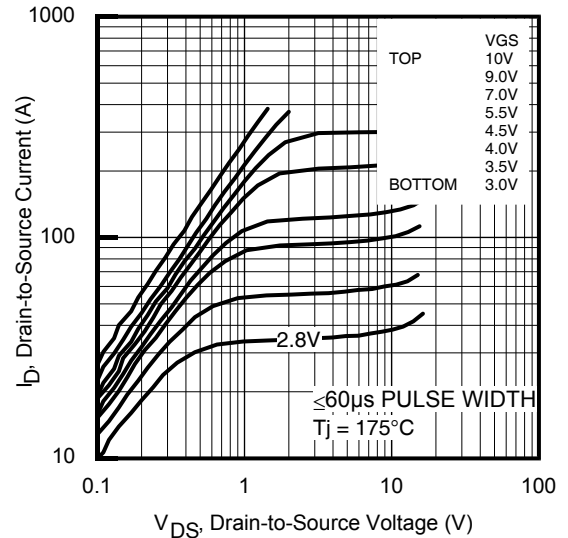
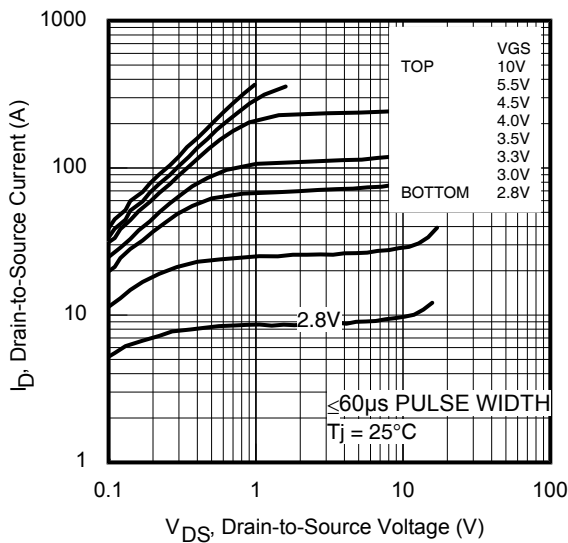


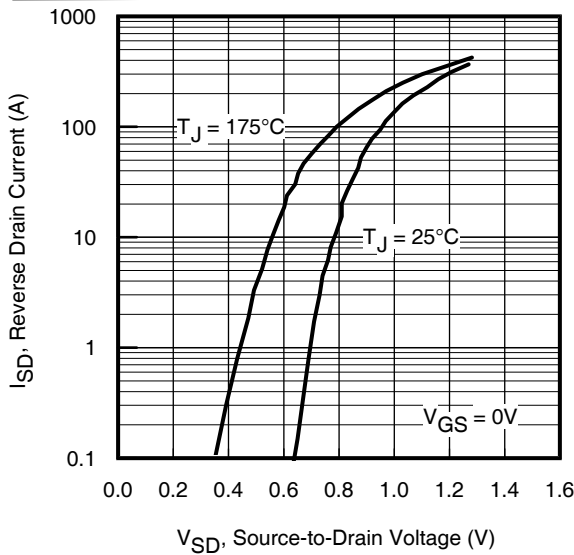
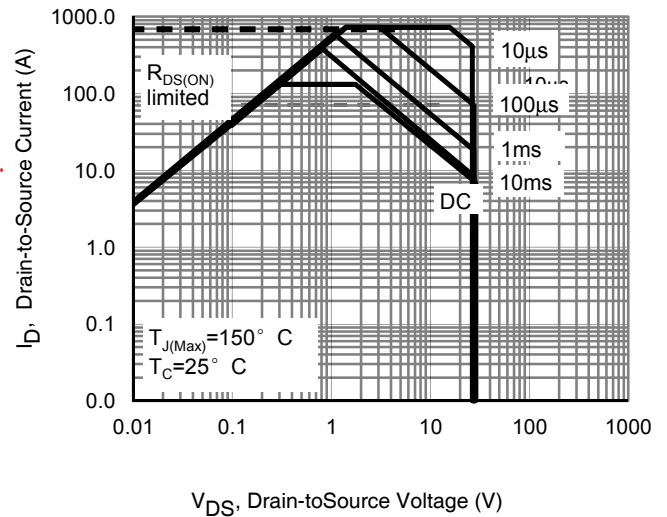
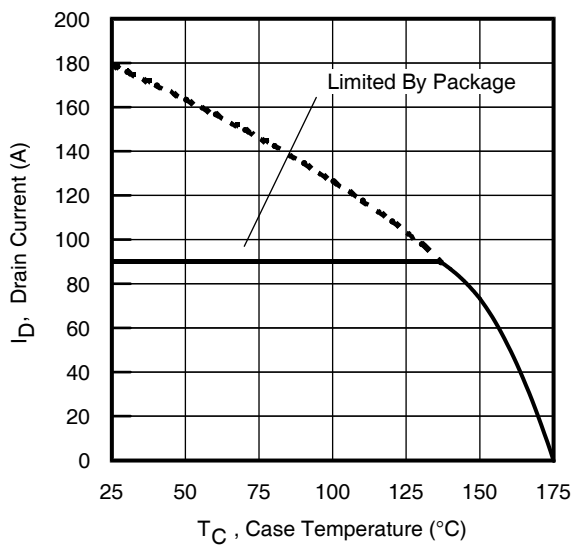
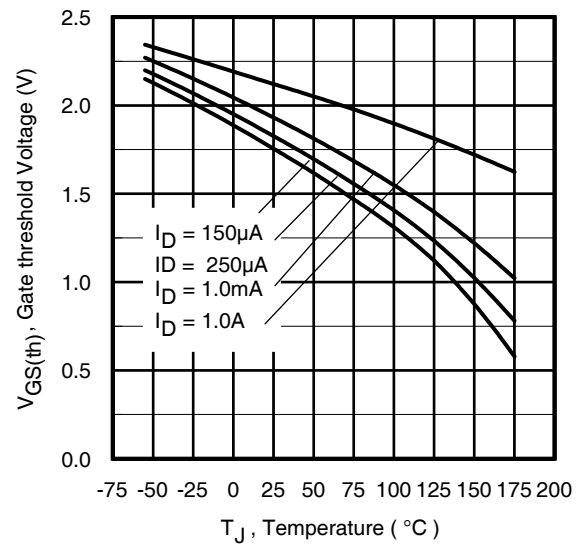
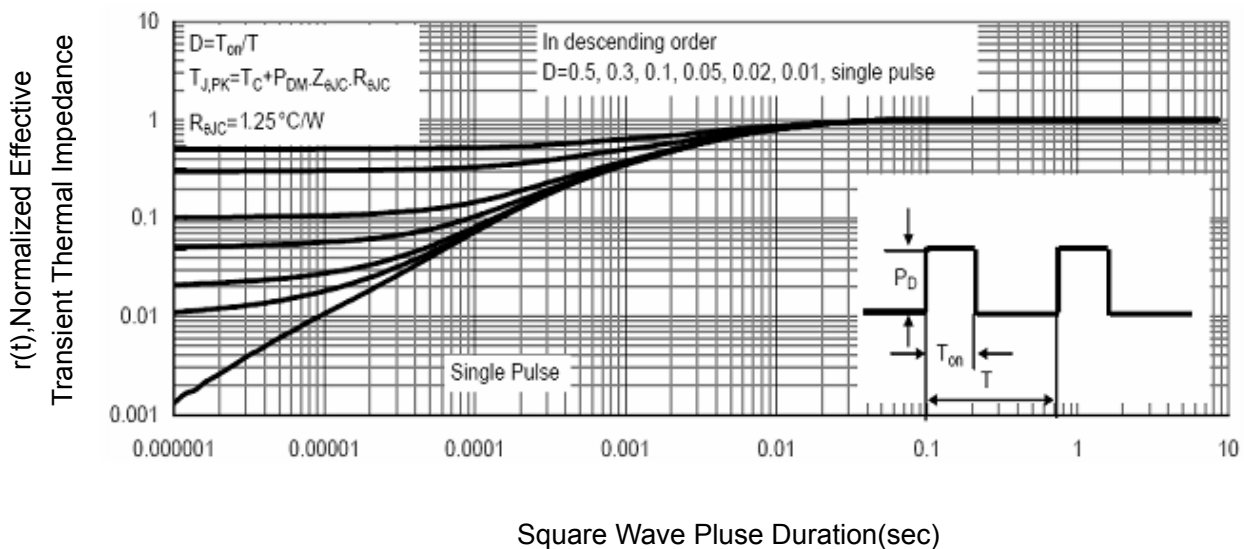
2) Gate charge test Circuit



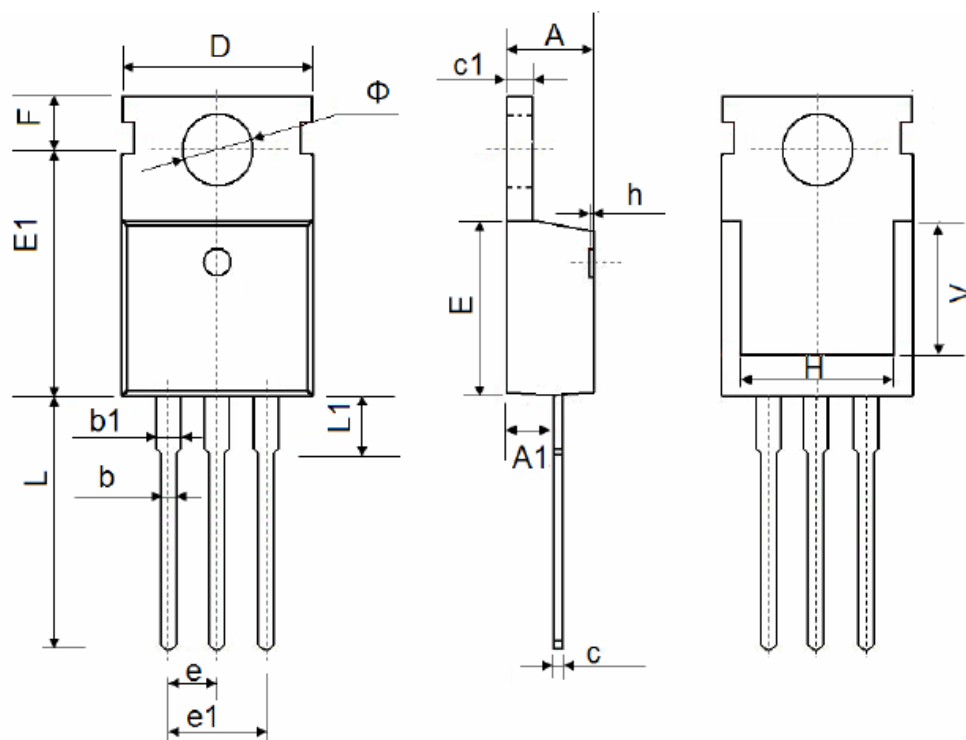
3) Switch Time Test Circuit



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Threshold Voltage vs. Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220 Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.400 | 4.600 | 0.173 | 0.181 |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 |
| b | 0.710 | 0.910 | 0.028 | 0.036 |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 |
| c | 0.330 | 0.650 | 0.013 | 0.026 |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 |
| D | 9.910 | 10.250 | 0.390 | 0.404 |
| E | 8.9500 | 9.750 | 0.352 | 0.384 |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 |
| e | 2.540 TYP. | | 0.100 TYP. | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 |
| F | 2.650 | 2.950 | 0.104 | 0.116 |
| H | 7.900 | 8.100 | 0.311 | 0.319 |
| h | 0.000 | 0.300 | 0.000 | 0.012 |
| L | 12.900 | 13.400 | 0.508 | 0.528 |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 |
| V | 7.500 REF. | | 0.295 REF. | |
| Φ | 3.400 | 3.800 | 0.134 | 0.150 |

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